

# 74HC4520-Q100; 74HCT4520-Q100

## Dual 4-bit synchronous binary counter

Rev. 1 — 4 December 2014

Product data sheet

### 1. General description

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The 74HC4520-Q100; 74HCT4520-Q100 are dual 4-bit internally synchronous binary counters with two clock inputs ( $\overline{nCP0}$  and  $\overline{nCP1}$ ). They have buffered outputs from all 4 bit positions ( $nQ0$  to  $nQ3$ ), and an asynchronous master reset input ( $\overline{nMR}$ ). The counter advances on either the LOW-to-HIGH transition of  $\overline{nCP0}$  when  $\overline{nCP1}$  is HIGH. It also advances on the HIGH-to-LOW transition of  $\overline{nCP1}$  if  $\overline{nCP0}$  is LOW. Either  $\overline{nCP0}$  or  $\overline{nCP1}$  may be used as the clock input to the counter. The other clock input may be used as a clock enable input. A HIGH on  $\overline{nMR}$  resets the counter ( $nQ0$  to  $nQ3 = \text{LOW}$ ) independent of  $\overline{nCP0}$  and  $\overline{nCP1}$ . Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

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- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Complies with JEDEC standard no. 7A
- Input levels:
  - ◆ For 74HC4520-Q100: CMOS level
  - ◆ For 74HCT4520-Q100: TTL level
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\text{ }\Omega$ )
- Multiple package options

### 3. Applications

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- Multistage synchronous counting
- Multistage asynchronous counting
- Frequency dividers



## 4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC4520D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT4520D-Q100				
74HC4520PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

## 5. Functional diagram

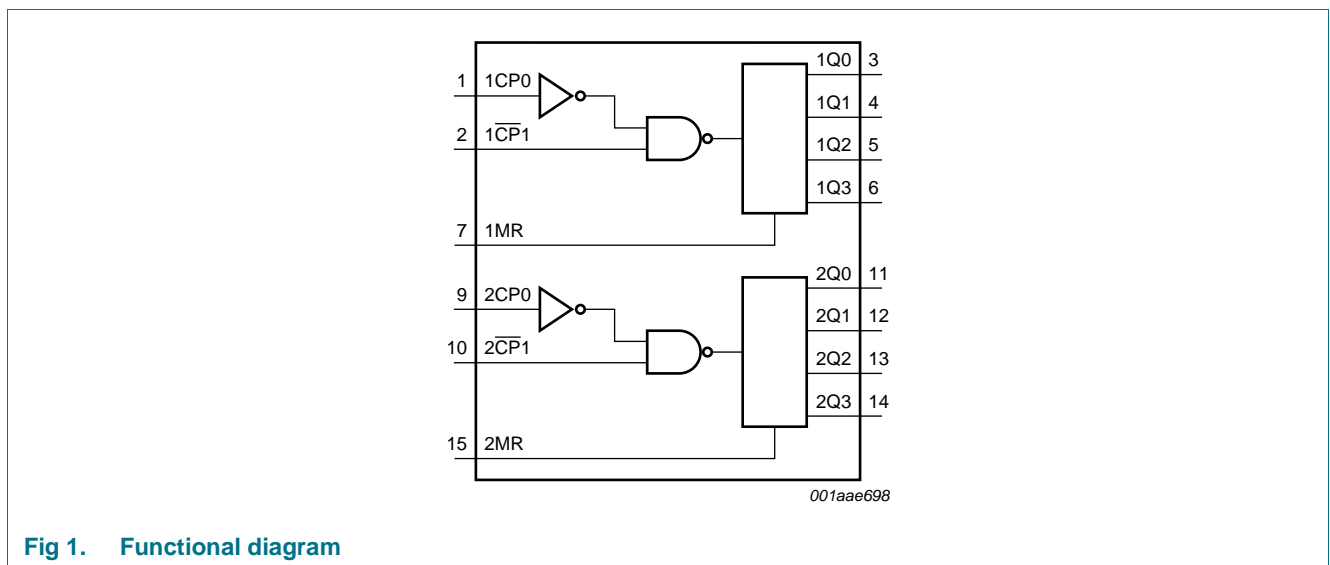


Fig 1. Functional diagram

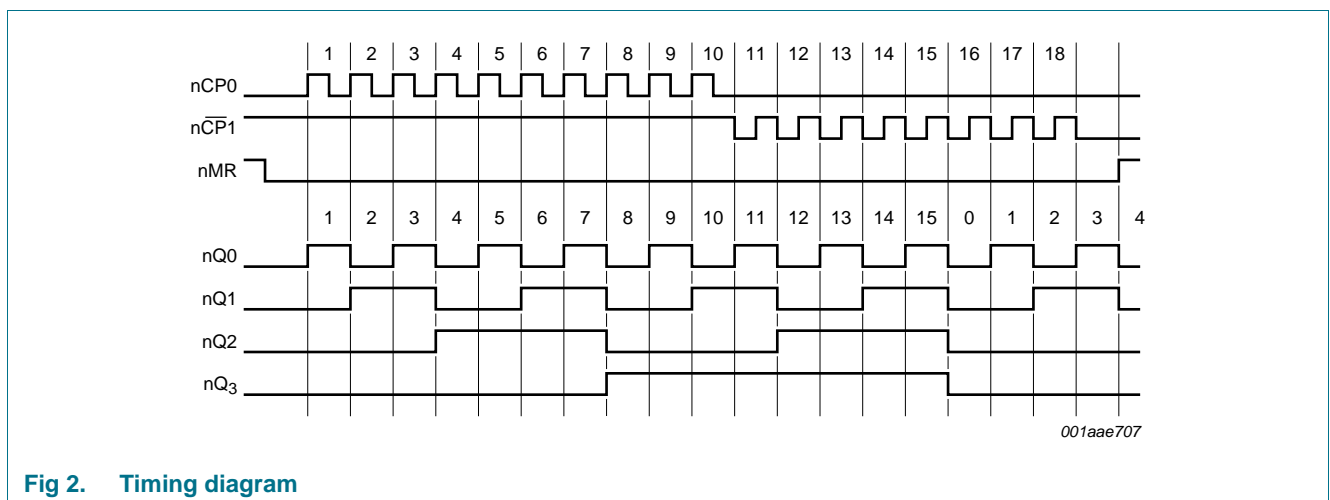


Fig 2. Timing diagram

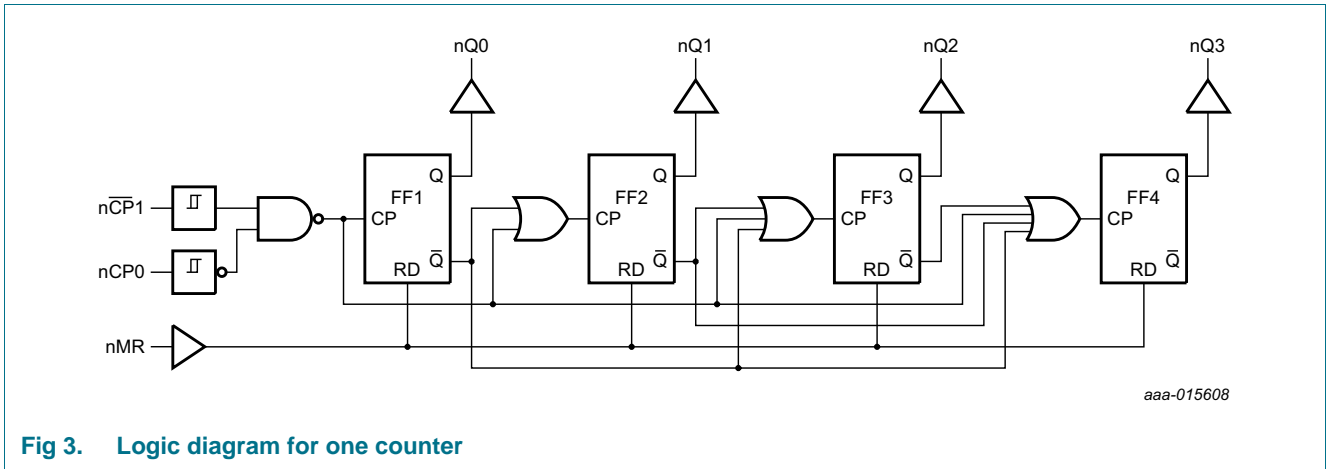


Fig 3. Logic diagram for one counter

## 6. Pinning information

### 6.1 Pinning

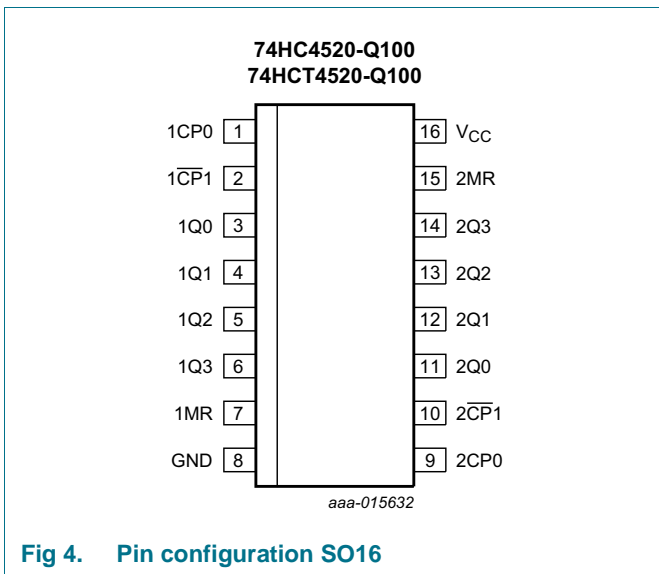


Fig 4. Pin configuration SO16

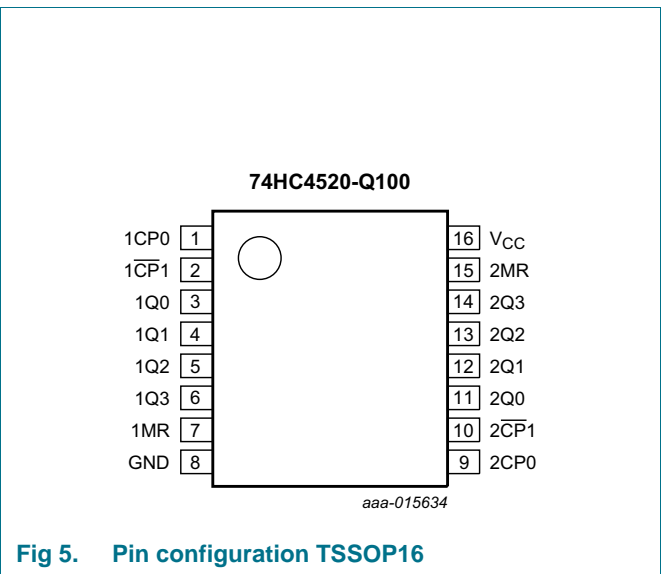


Fig 5. Pin configuration TSSOP16

### 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP0, 2CP0	1, 9	clock input (LOW-to-HIGH edge-triggered)
1CP1, 2CP1	2, 10	clock input (HIGH-to-LOW edge-triggered)
1Q0 to 1Q3	3, 4, 5, 6	output
1MR, 2MR	7, 15	asynchronous master reset input (active HIGH)
GND	8	ground (0 V)
2Q0 to 2Q3	11, 12, 13, 14	output
V <sub>CC</sub>	16	supply voltage

## 7. Functional description

Table 3. Function table<sup>[1]</sup>

nCP0	nCP1	nMR	Mode
↑	H	L	counter advances
L	↓	L	counter advances
↓	X	L	no change
X	↑	L	no change
↑	L	L	no change
H	↓	L	no change
X	X	H	nQ0 to nQ3 = LOW

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.

## 8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	±20	mA
$I_{OK}$	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	±20	mA
$I_O$	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	-	±25	mA
$I_{CC}$	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	SO16 and TSSOP16 packages <sup>[1]</sup>	-	500	mW

[1] For SO16 package: above 70 °C the value of  $P_{tot}$  derates linearly at 8 mW/K.  
For TSSOP16 package: above 60 °C the value of  $P_{tot}$  derates linearly at 5.5 mW/K.

## 9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC4520-Q100			74HCT4520-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC4520-Q100</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I <sub>O</sub> = -4.0; V <sub>CC</sub> = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
I <sub>O</sub> = -5.2; V <sub>CC</sub> = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V		
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	8.0	-	80.0	-	160.0	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HCT4520-Q100</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	8.0	-	80.0	-	160.0	μA
ΔI <sub>CC</sub>	additional supply current	per input pin; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A								
		pin nCP0, nCP1	-	80	288	-	360	-	392	μA
		pin nMR	-	150	540	-	675	-	735	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF

## 11. Dynamic characteristics

**Table 7. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC4520-Q100</b>										
t <sub>pd</sub>	propagation delay	nCP0 to nQn; see <a href="#">Figure 6</a> <sup>[1]</sup>								
		V <sub>CC</sub> = 2.0 V	-	77	240	-	300	-	360	ns
		V <sub>CC</sub> = 4.5 V	-	28	48	-	60	-	72	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	24	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	22	41	-	51	-	61	ns
		nCP1 to nQn; see <a href="#">Figure 6</a> <sup>[1]</sup>								
		V <sub>CC</sub> = 2.0 V	-	77	240	-	300	-	360	ns
		V <sub>CC</sub> = 4.5 V	-	28	48	-	60	-	72	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	24	-	-	-	-	-	ns
V <sub>CC</sub> = 6.0 V	-	22	41	-	51	-	61	ns		

**Table 7. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V);  $C_L = 50$  pF unless otherwise specified; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PHL</sub>	HIGH to LOW propagation delay	nMR to nQn; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	-	44	150	-	190	-	225	ns
		V <sub>CC</sub> = 4.5 V	-	16	30	-	38	-	45	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	13	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	13	26	-	33	-	38	ns
t <sub>t</sub>	transition time	nQn; see <a href="#">Figure 6</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		V <sub>CC</sub> = 6.0 V	-	6	13	-	16	-	19	ns
t <sub>w</sub>	pulse width	nCP0, nCP1 HIGH or LOW; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	80	22	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	8	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	6	-	17	-	20	-	ns
		nMR HIGH; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	120	39	-	150	-	180	-	ns
		V <sub>CC</sub> = 4.5 V	24	14	-	30	-	36	-	ns
		V <sub>CC</sub> = 6.0 V	20	11	-	26	-	31	-	ns
t <sub>rec</sub>	recovery time	nMR to nCP0, nCP1; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	0	-28	-	0	-	0	-	ns
		V <sub>CC</sub> = 4.5 V	0	-10	-	0	-	0	-	ns
		V <sub>CC</sub> = 6.0 V	0	-8	-	0	-	0	-	ns
t <sub>su</sub>	set-up time	nCP0 to nCP1; nCP1 to nCP0; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	80	14	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	5	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	4	-	17	-	20	-	ns
f <sub>max</sub>	maximum frequency	nCP0, nCP1; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 2.0 V	6	19	-	4.8	-	4	-	MHz
		V <sub>CC</sub> = 4.5 V	30	58	-	24	-	20	-	MHz
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	68	-	-	-	-	-	MHz
		V <sub>CC</sub> = 6.0 V	35	69	-	28	-	24	-	MHz
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 5 V; <sup>[3]</sup> f <sub>i</sub> = 1 MHz	-	29	-	-	-	-	-	pF
<b>74HCT4520-Q100</b>										
t <sub>pd</sub>	propagation delay	nCP0 to nQn; see <a href="#">Figure 6</a> <sup>[1]</sup>								
		V <sub>CC</sub> = 4.5 V	-	28	53	-	66	-	80	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	24	-	-	-	-	-	ns
		nCP1 to nQn; see <a href="#">Figure 6</a> <sup>[1]</sup>								
		V <sub>CC</sub> = 4.5 V	-	25	53	-	66	-	80	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	24	-	-	-	-	ns	

**Table 7. Dynamic characteristics ...continued**

*Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit, see [Figure 7](#).*

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PHL</sub>	HIGH to LOW propagation delay	nMR to nQn; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 4.5 V	-	16	35	-	44	-	53	ns
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	13	-	-	-	-	-	ns
t <sub>t</sub>	transition time	nQn; see <a href="#">Figure 6</a> [2]								
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
t <sub>W</sub>	pulse width	nCP0, nCP1 HIGH or LOW; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 4.5 V	20	10	-	25	-	30	-	ns
		nMR HIGH; see <a href="#">Figure 6</a>								
t <sub>rec</sub>	recovery time	nMR to nCP0, nCP1; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 4.5 V	0	-8	-	0	-	0	-	ns
t <sub>su</sub>	set-up time	nCP0 to nCP1; nCP1 to nCP0; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 4.5 V	16	6	-	20	-	24	-	ns
f <sub>max</sub>	maximum frequency	nCP0, nCP1; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 4.5 V	30	58	-	24	-	20	-	MHz
		V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	64	-	-	-	-	-	MHz
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> - 1.5 V; V <sub>CC</sub> = 5 V; f <sub>i</sub> = 1 MHz [3]	-	24	-	-	-	-	-	pF

[1] t<sub>pd</sub> is the same as t<sub>PHL</sub> and t<sub>PLH</sub>.

[2] t<sub>t</sub> is the same as t<sub>THL</sub> and t<sub>TLH</sub>.

[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

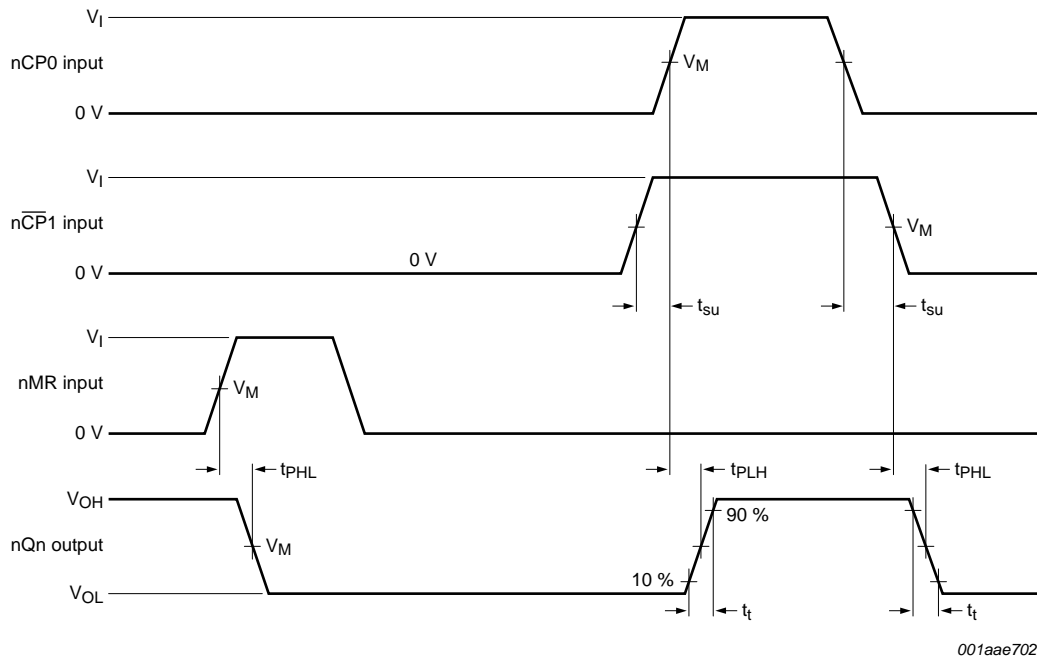
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

∑(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of outputs.

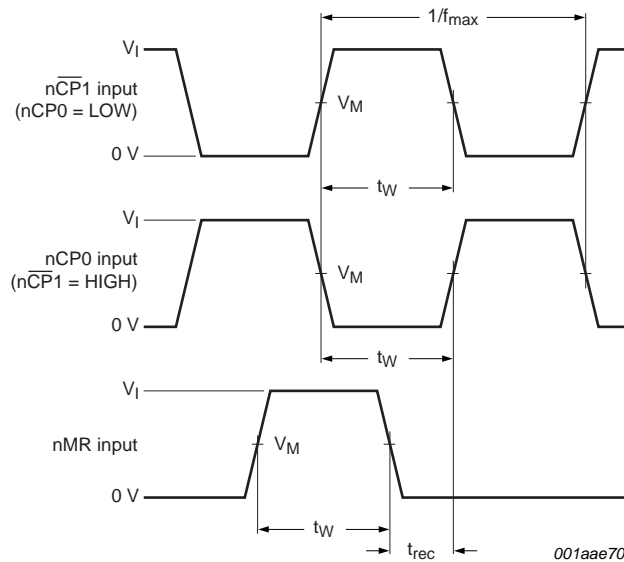


12. Waveforms



001aae702

a. nCP0 and nCP1 set-up times, propagation delays and output transition times



001aae701

b. nMR recovery time, minimum nCP0, nCP1, nMR pulse widths and maximum frequency

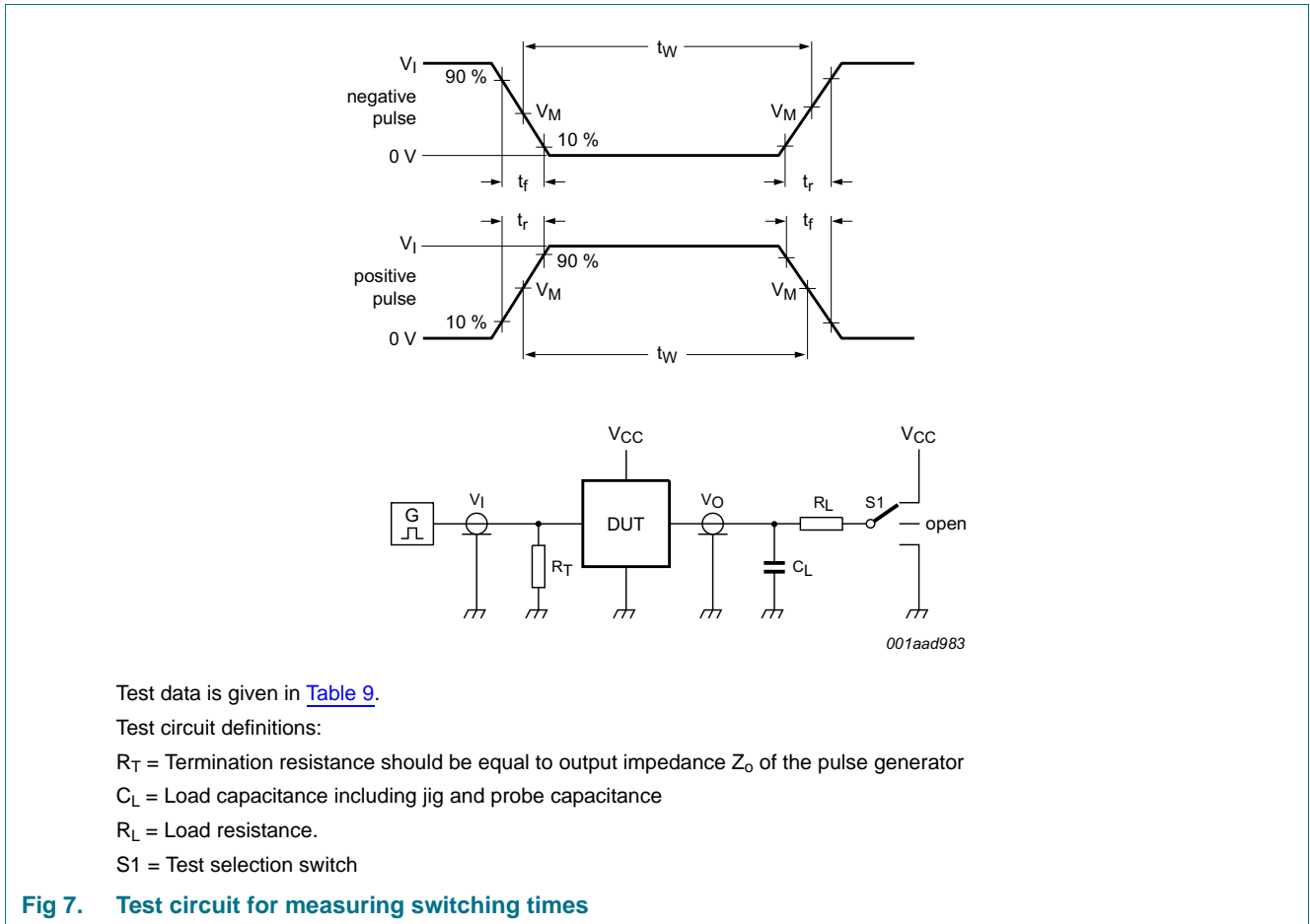
Measurement points are given in [Table 8](#).

The logic levels  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels that occur with the output load.

Fig 6. Waveforms showing measurements for switching times

**Table 8. Measurement points**

Type	Input		Output
	$V_M$	$V_I$	$V_M$
74HC4520-Q100	$0.5 \times V_{CC}$	GND to $V_{CC}$	$0.5 \times V_{CC}$
74HCT4520-Q100	1.3 V	GND to 3 V	1.3 V



**Table 9. Test data**

Type	Input		Load		S1 position
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$
74HC4520-Q100	$V_{CC}$	6 ns	15 pF, 50 pF	1 k $\Omega$	open
74HCT4520-Q100	3 V	6 ns	15 pF, 50 pF	1 k $\Omega$	open

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

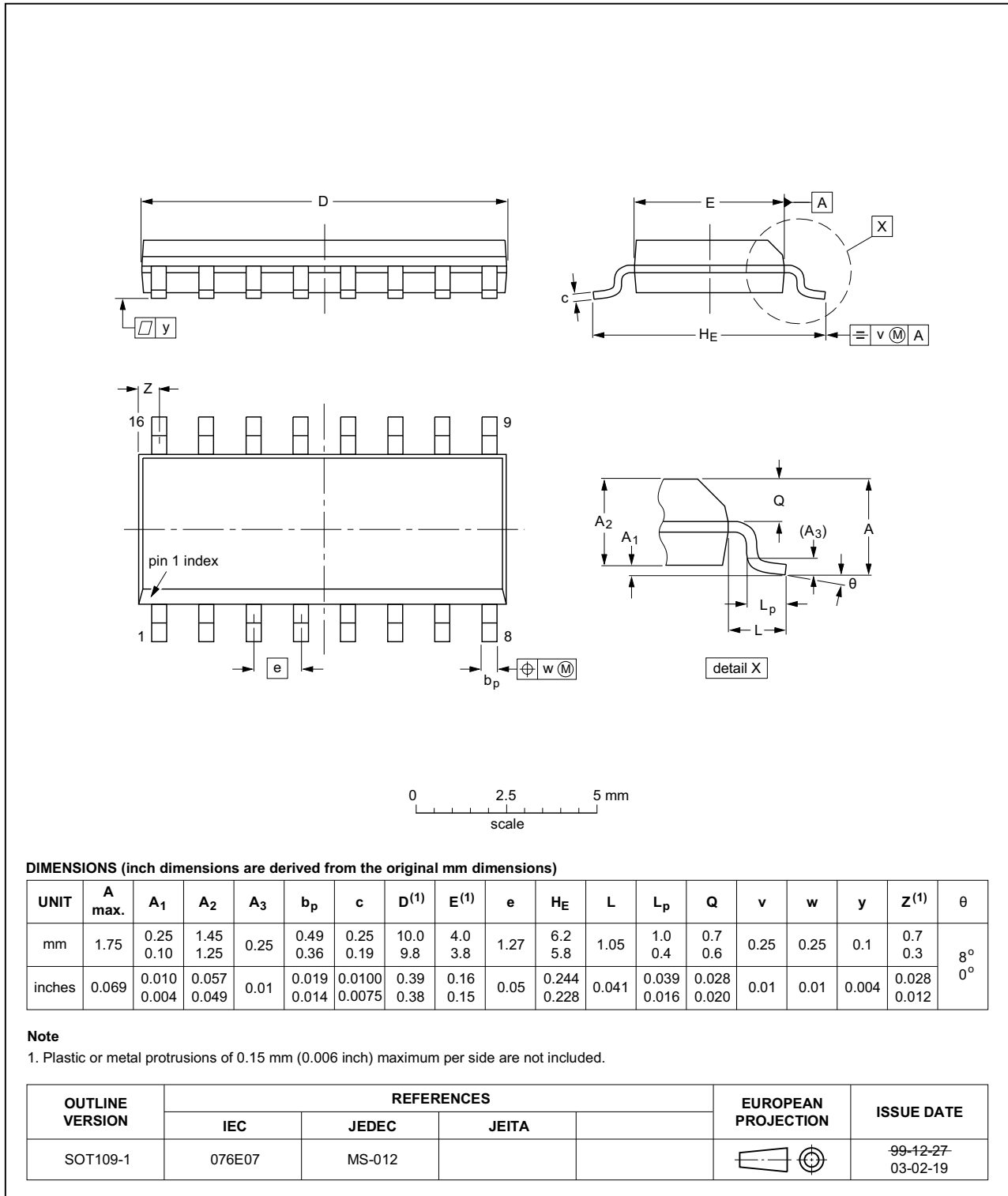


Fig 8. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

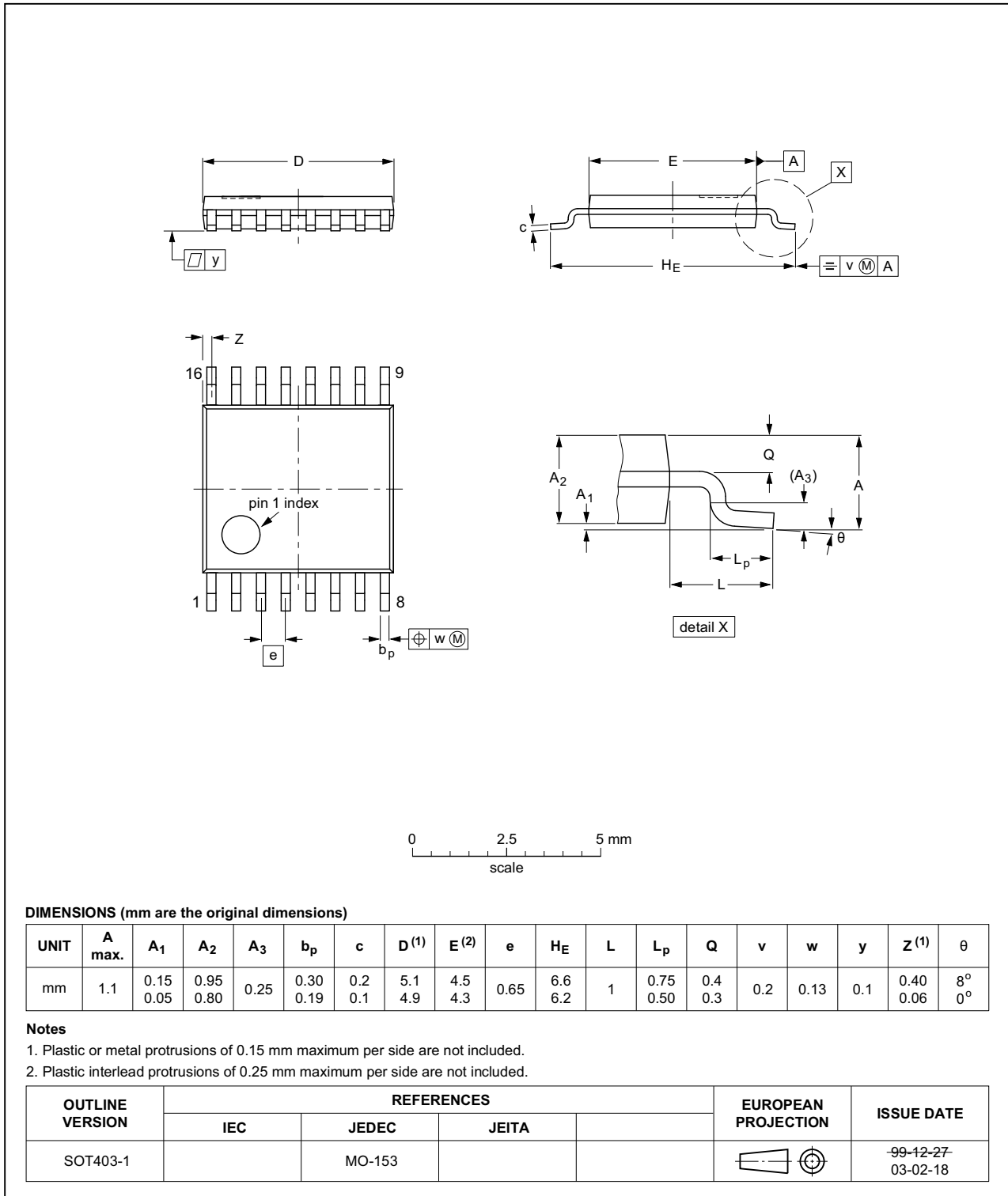


Fig 9. Package outline SOT403-1 (TSSOP16)

## 14. Abbreviations

**Table 10. Abbreviations**

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

**Table 11. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4520_Q100 v.1	20141204	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 4 December 2014  
 Document identifier: 74HC\_HCT4520\_Q100